

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
-20V	1.9mΩ @ V _{GS} = -10V	-60A
	2.4mΩ @ V _{GS} = -4.5V	-60A
	3.8mΩ @ V _{GS} = -2.5V	-60A

Description

This new generation P-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} and yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

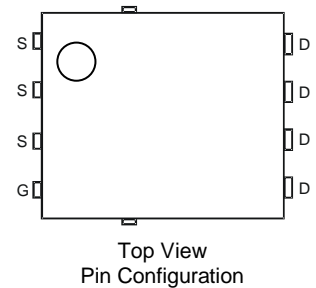
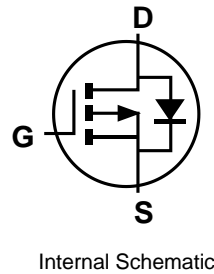
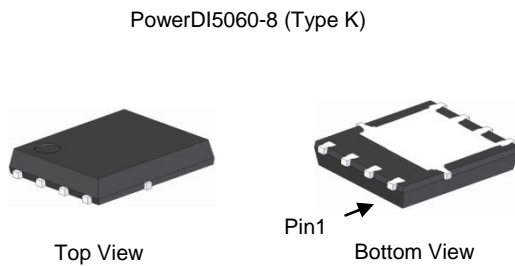
- Switch

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- <1.1mm Package Profile – Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: PowerDI5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208③
- Weight: 0.097 grams (Approximate)

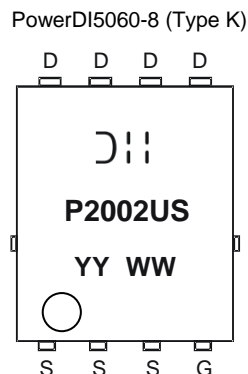


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2002UPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

- Notes:
- EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current, V _{GS} = -10V (Note 5)	Steady State (Note 8)	T _C = +25°C T _C = +70°C	I _D	-60 -60	A
	t < 10s	T _A = +25°C T _A = +70°C		-42 -33.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	-100	A
Continuous Body Diode Forward Current (Note 5)	Steady State (Note 8)	T _C = +25°C	I _S	-60	A
	t < 10s	T _A = +25°C		-5.6	A
Pulsed Body Diode Forward Current (10µs pulse, duty cycle = 1%)			I _{SM}	-100	A
Avalanche Current, L = 0.1mH			I _{AS}	-37	A
Avalanche Energy, L = 0.1mH			E _{AS}	69.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P _D	2.3	W
	t < 10s		6.25	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	55	°C/W
	t < 10s		20	
Total Power Dissipation (Note 5)	Steady State	P _D	104	W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	0.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	—	-1.4	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.3	1.9	mΩ	V _{GS} = -10V, I _D = -25A
		—	1.5	2.4		V _{GS} = -4.5V, I _D = -20A
		—	2	3.8		V _{GS} = -2.5V, I _D = -15A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	12826	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	2547	—		
Reverse Transfer Capacitance	C _{rss}	—	1924	—		
Gate Resistance	R _G	0.9	4.2	6.6	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	476	585	nC	V _{DS} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	228	282		
Gate-Source Charge	Q _{gs}	—	24.8	—		
Gate-Drain Charge	Q _{gd}	—	61.9	—		
Turn-On Delay Time	t _{D(ON)}	—	14.2	28	ns	V _{DD} = -10V, V _{GEN} = -4.5V, R _{GEN} = 1Ω, I _D = -10A
Turn-On Rise Time	t _R	—	35.4	70		
Turn-Off Delay Time	t _{D(OFF)}	—	361	578		
Turn-Off Fall Time	t _F	—	224	358		
BODY DIODE CHARACTERISTICS						
Continuous Body Diode Forward Current (Notes 5 & 8)	I _S	—	—	-60	A	T _C = +25°C
Diode Forward Voltage	V _{SD}	—	-0.58	-1.1	V	V _{GS} = 0V, I _S = -5A
Reverse Recovery Time (Note 7)	t _{RR}	—	137	219	ns	I _F = -10A, di/dt = 100A/μs
Reverse Recovery Charge (Note 7)	Q _{RR}	—	221	332	nC	
Reverse Recovery Fall Time (Note 7)	t _A	—	39	—	ns	
Reverse Recovery Raise Time (Note 7)	t _B	—	98	—		

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to product testing.
 8. Package limited.

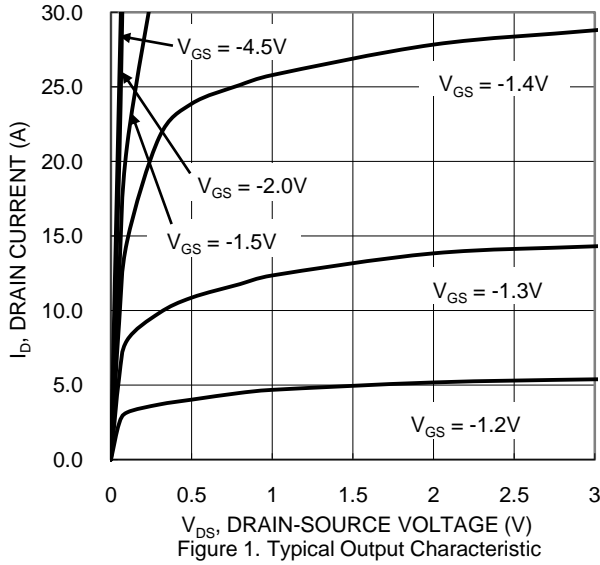


Figure 1. Typical Output Characteristic

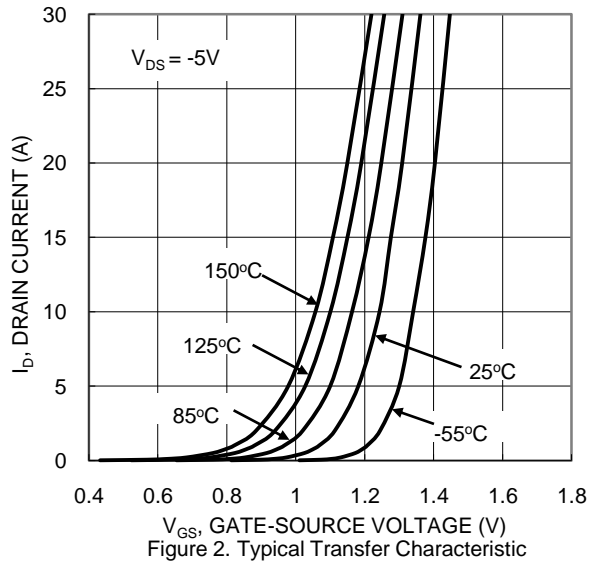


Figure 2. Typical Transfer Characteristic

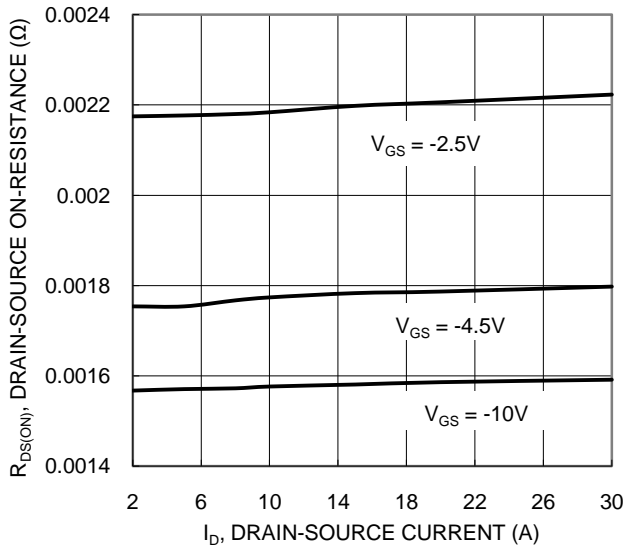


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

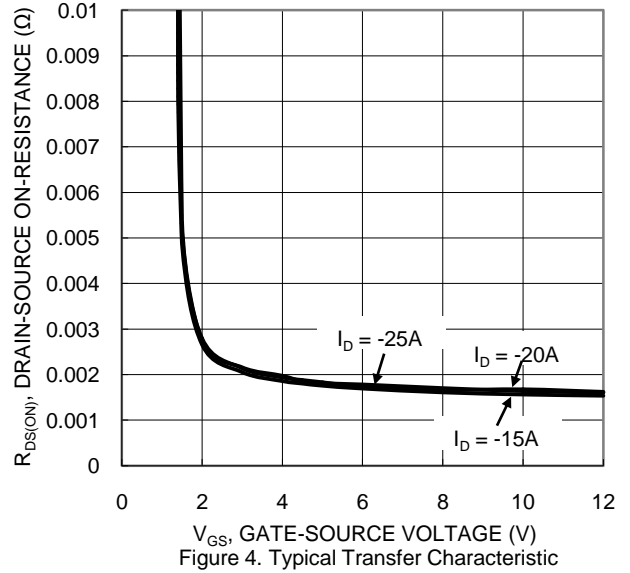


Figure 4. Typical Transfer Characteristic

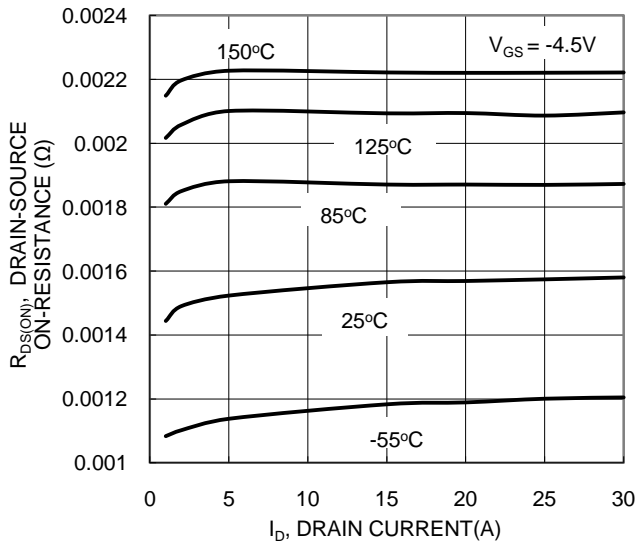


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

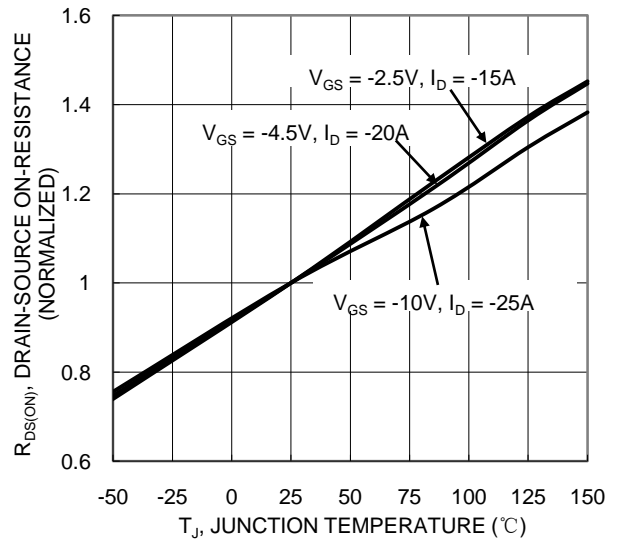


Figure 6. On-Resistance Variation with Temperature

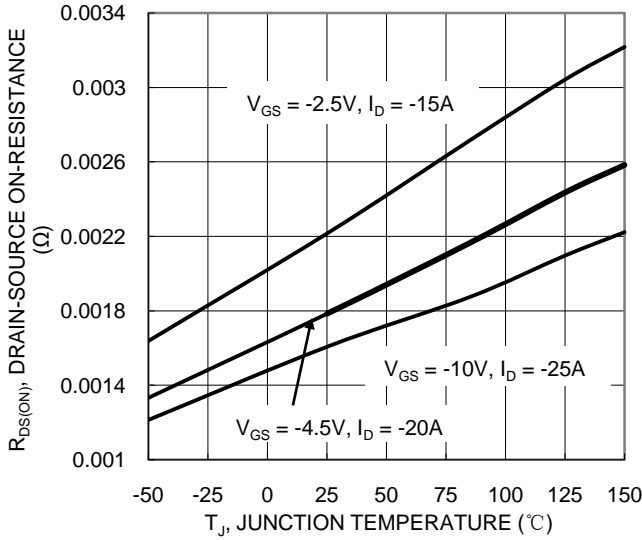


Figure 7. On-Resistance Variation with Temperature

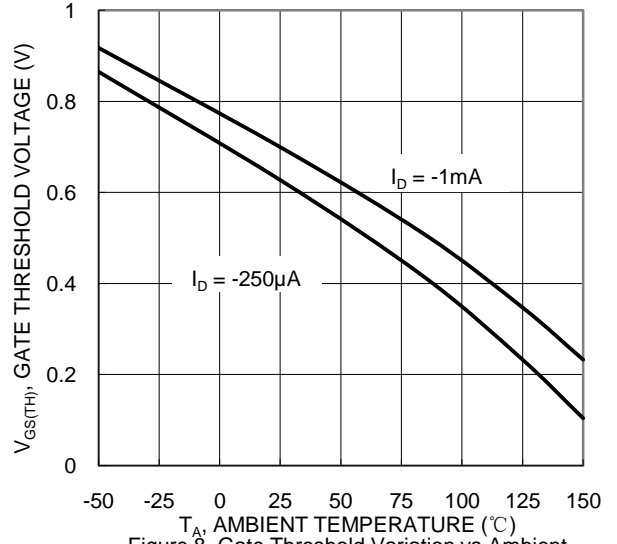


Figure 8. Gate Threshold Variation vs Ambient Temperature

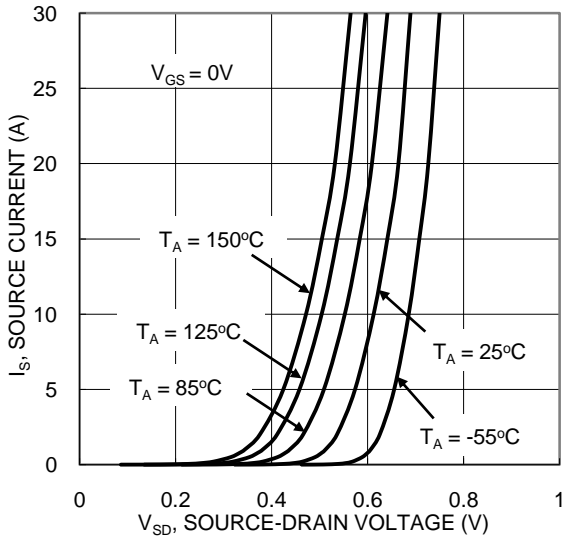


Figure 9. Diode Forward Voltage vs. Current

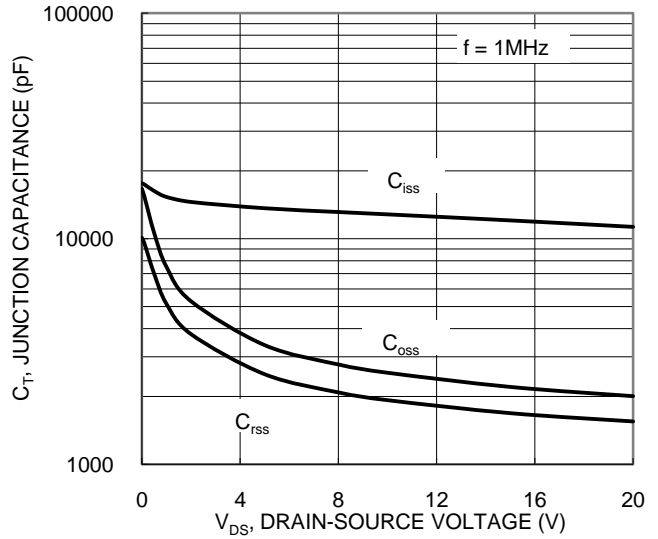


Figure 10. Typical Junction Capacitance

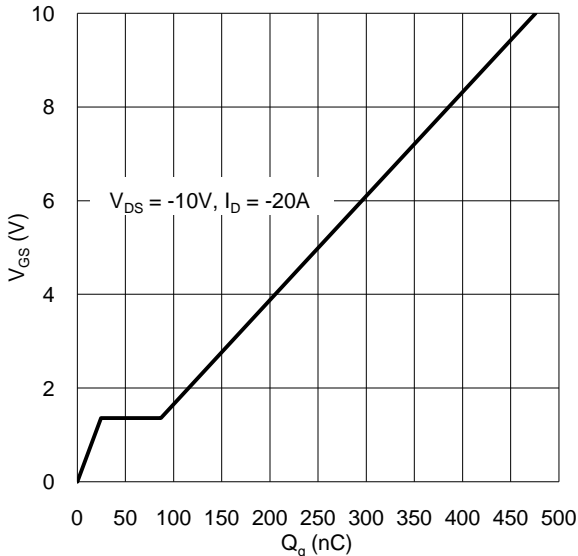


Figure 11. Gate Charge

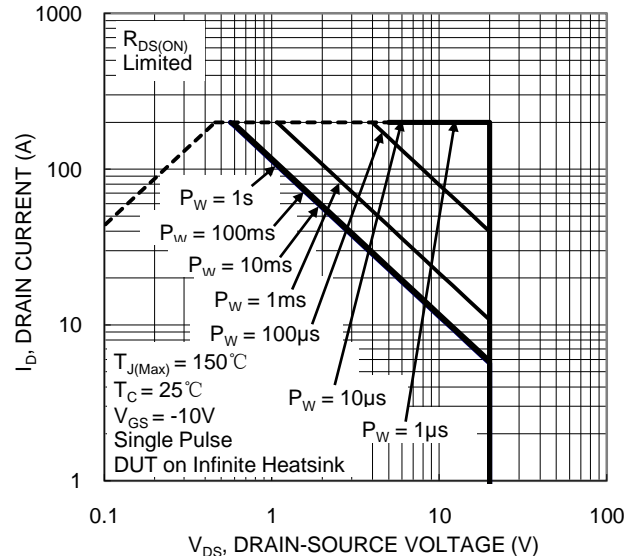


Figure 12. SOA, Safe Operation Area

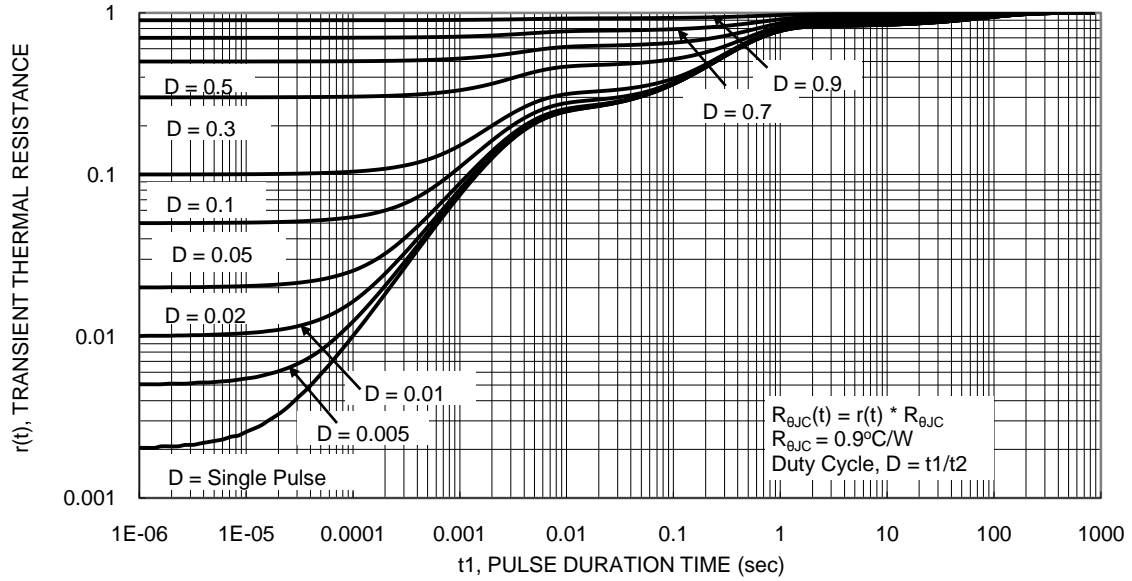
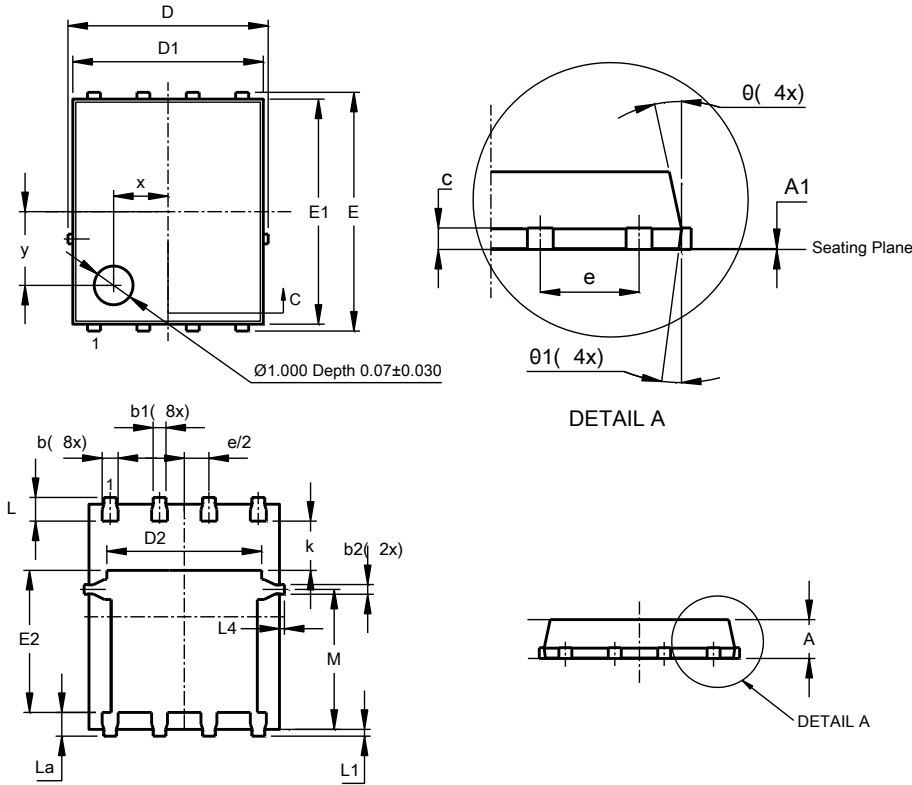


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

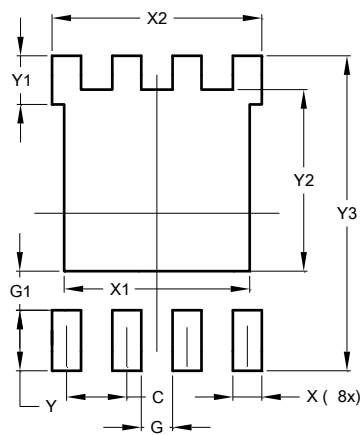


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
E	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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